

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET 5LN01SS — General-Purpose Switching Device **Applications**

Features

- · Low ON-resistance
- Ultrahigh-speed switching
- 2.5V drive

Specifications

Absolute Maximum Ratings at Ta=25°C

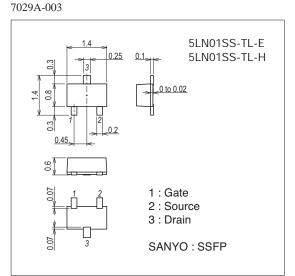
| Parameter | Symbol | Conditions | Ratings | Unit |
|-----------------------------|------------------|------------------------|-------------|------|
| Drain-to-Source Voltage | VDSS | | 50 | V |
| Gate-to-Source Voltage | V _{GSS} | | ±10 | V |
| Drain Current (DC) | ID | | 0.1 | А |
| Drain Current (Pulse) | IDP | PW≤10µs, duty cycle≤1% | 0.4 | А |
| Allowable Power Dissipation | PD | | 0.15 | W |
| Channel Temperature | Tch | | 150 | °C |
| Storage Temperature | Tstg | | -55 to +150 | °C |

This product is designed to "ESD immunity < 200V*", so please take care when handling.

* Machine Model

Package Dimensions

unit : mm (typ)

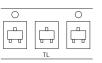


Product & Package Information

- Package : SSFP
- JEITA, JEDEC : SC-81
- Minimum Packing Quantity : 8,000 pcs./reel

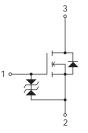
Packing Type: TL

Marking





Electrical Connection



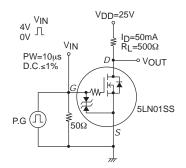
SANYO Semiconductor Co., Ltd. http://semicon.sanyo.com/en/network

62712 TKIM/31506PE MSIM TB-00002117/82200 TSIM TA-2065 No.6560-1/7

| Electrical Characteristics at Ta=25°C | 1 |
|---------------------------------------|---|
|---------------------------------------|---|

| Parameter | Symbol | Conditions | | Ratings | | |
|--|-----------------------|---|-------------|---------|-----|------|
| Parameter | | Conditions | min | typ | max | Unit |
| Drain-to-Source Breakdown Voltage | V(BR)DSS | ID=1mA, VGS=0V | 50 | | | V |
| Zero-Gate Voltage Drain Current | IDSS | VDS=50V, VGS=0V | | | 1 | μΑ |
| Gate-to-Source Leakage Current | IGSS | V _{GS} =±8V, V _{DS} =0V | | | ±10 | μΑ |
| Cutoff Voltage | VGS(off) | VDS=10V, ID=100µA | 0.4 | | 1.3 | V |
| Forward Transfer Admittance | yfs | V _{DS} =10V, I _D =50mA | 0.13 | 0.18 | | S |
| | R _{DS} (on)1 | ID=50mA, VGS=4V | | 6 | 7.8 | Ω |
| Static Drain-to-Source On-State Resistance | R _{DS} (on)2 | I _D =30mA, V _{GS} =2.5V | | 7.1 | 9.9 | Ω |
| | R _{DS} (on)3 | ID=10mA, VGS=1.5V | A, VGS=1.5V | | 20 | Ω |
| Input Capacitance | Ciss | | | 6.6 | | pF |
| Output Capacitance | Coss | V _{DS} =10V, f=1MHz | | 4.7 | | pF |
| Reverse Transfer Capacitance | Crss | | | 1.7 | | pF |
| Turn-ON Delay Time | t _d (on) | | | 18 | | ns |
| Rise Time | tr | Concernencificati Track Olanovik | | 42 | | ns |
| Turn-OFF Delay Time | t _d (off) | See specified Test Circuit. | | 190 | | ns |
| Fall Time | tf | | | 105 | | ns |
| Total Gate Charge | Qg | | | 1.57 | | nC |
| Gate-to-Source Charge | Qgs | V _{DS} =10V, V _{GS} =10V, I _D =100mA | | 0.20 | | nC |
| Gate-to-Drain "Miller" Charge | Qgd | 1 | | 0.32 | | nC |
| Diode Forward Voltage | V _{SD} | I _S =100mA, V _{GS} =0V | | 0.85 | 1.2 | V |

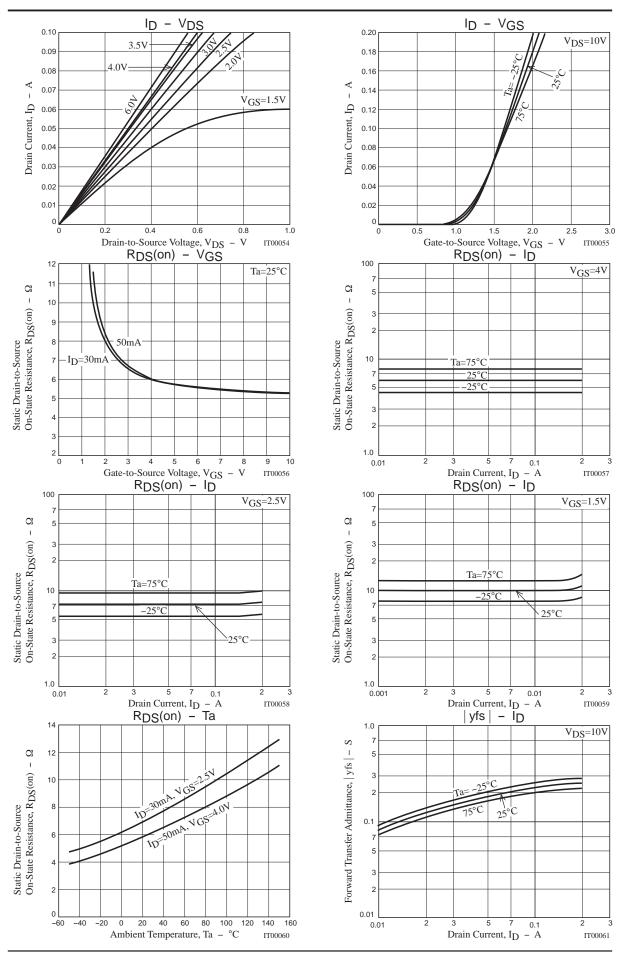
Switching Time Test Circuit



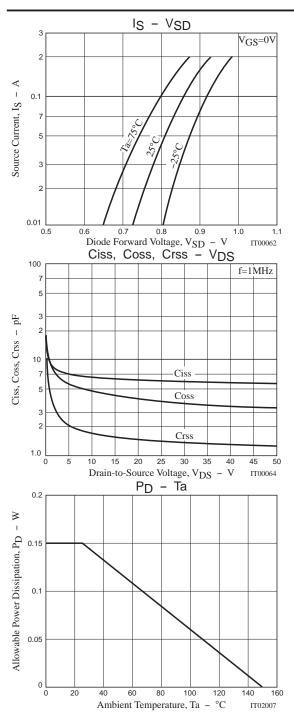
Ordering Information

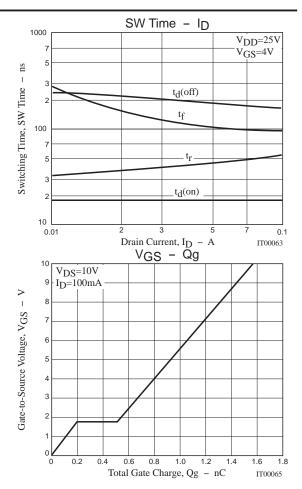
| Device | Pevice Package Shipping | | memo | |
|--------------|-------------------------|----------------|--------------------------|--|
| 5LN01SS-TL-E | SSFP | 8,000pcs./reel | Pb Free | |
| 5LN01SS-TL-H | SSFP | 8,000pcs./reel | Pb Free and Halogen Free | |

5LN01SS



5LN01SS





Embossed Taping Specification

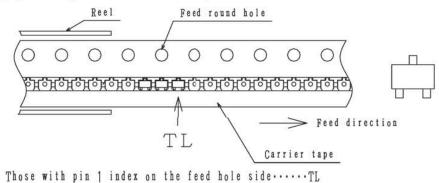
5LN01SS-TL-E, 5LN01SS-TL-H

1. Packing Format

| Package Name | Carrier Tape | Maximum Number of devices contained (pcs) | | Packing format | | |
|--------------|--------------|--|---------------------------------------|--|--|--|
| | Туре | Reel Inner bo | x Outer box | Inner BOX (C-1) | Outer BOX (A-7) | |
| SSFP SSFP | | 8,000 40,00 | , 000 240, 000 | 5 reels contained | 6 inner boxes contained | |
| | | | | Dimensions:mm (external) | Dimension::mm (external) | |
| | | | | 183×72×185 | 440×195×210 | |
| | | Ree | l label, In | ner box label Oute | r box label | |
| Packing met | thod | | (un i | t:mm) It is a The for distril | a label at the time of factory shipm m of a label may change in physical bution process. | |
| ° | | L | 6 9 | | 108 | |
| | | Ľ | m mms | | | |
| | //// Type | 0 20040204020 | (P) TYPE 00000 | | 8 CODB + | |
| | LOT | No> | | | uuuu | |
| | ///// Quan | tity -> | (a) (TY 0, 000 | | O, OOO PUS LEAD FREE # | |
| | /// | c | (2) (PECIAL | | | |
| | Orig | in → | * Z 0 7 2 2 0 0 ASSEMELY: **** (DI | 91901 | | |
| | | Î | NOTE (1) | V ASS | *20722005)10C* MBLY:***** (DIFFUSION:******) | |
| 1 | Reel la | bel | The LEAD F | REE # description shows t of the terminal is lead f | hat the surface ree | |
| | | | Labe | 201 (1998) ADDIAL CONTRACT (FAMILY AND A CONTRACTOR DATE | | |
| | | | LEAD FR | | | |
| | | | LEAD FR | EE 4 JEITA Phase 3 | | |
| 2. Taping | configu | ration | | | | |
| 2-1. Car | rier tape | size (unit | : :mm) | | | |
| | When a d | evice is moun | tel \$ 1. | 55±0.05 4. 0±0.03 | 7 5 ±0. 04 5 ±0. 04 0 ±0. 05 | |
| | 0.35 | | ¢0.5 | ±0. 05 2. 0±0. 04 | 7 5 ± 0. 0 5 ± 0. 04 0 ± 0. 05 | |
| | / | | | | * m œ | |
| | | | 1111 | | | |
| | / | (⊕∥⊕ | $-\Phi + \Phi +$ | <u>-</u> �- <u> �, � </u> | | |
| - | 1 + | | मक्रिक्सके | | संग्रही — | |
| | | | -1-1-101 | | <u> </u> | |
| (0.80) | 0 ±0. 05 | | 25±0.03 | | ↑ 0±0.03 | |



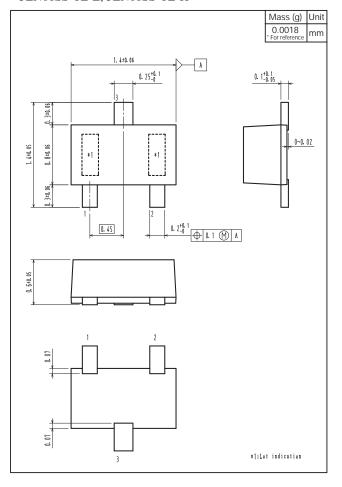
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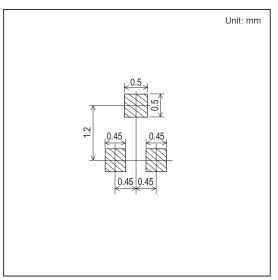
1. 50±0.03

Device mounting recess square hole

Outline Drawing 5LN01SS-TL-E, 5LN01SS-TL-H



Land Pattern Example



Note on usage : Since the 5LN01SS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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